



- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

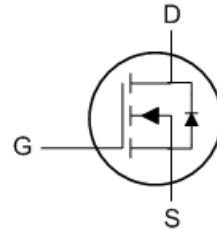
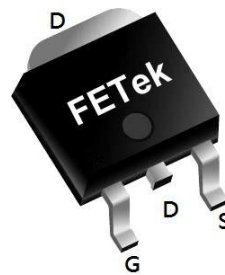
**Product Summary**

BVDSS	RDSON	ID
150V	46mΩ	30A

**Description**

The FKD28N15 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The FKD28N15 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

**TO252 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	150	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	22	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	60	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	216	mJ
$I_{AS}$	Avalanche Current	38	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation <sup>3</sup>	115	W
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 175	$^\circ C$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	55	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	1.3	$^\circ C/W$

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	150	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=20A$	---	35	46	$m\Omega$
	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=4.5V, I_D=20A$	---	37	50	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=120V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=120V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=20A$	---	55	---	S
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=75V, V_{GS}=4.5V, I_D=10A$	---	40	---	nC
$Q_{gs}$	Gate-Source Charge		---	10	---	
$Q_{gd}$	Gate-Drain Charge		---	21	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V, V_{GS}=4.5V, R_G=3.3\Omega, I_D=10A$	---	18	---	ns
$T_r$	Rise Time		---	20	---	
$T_{d(off)}$	Turn-Off Delay Time		---	65	---	
$T_f$	Fall Time		---	15	---	
$C_{iss}$	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	3755	---	pF
$C_{oss}$	Output Capacitance		---	207	---	
$C_{rss}$	Reverse Transfer Capacitance		---	160	---	

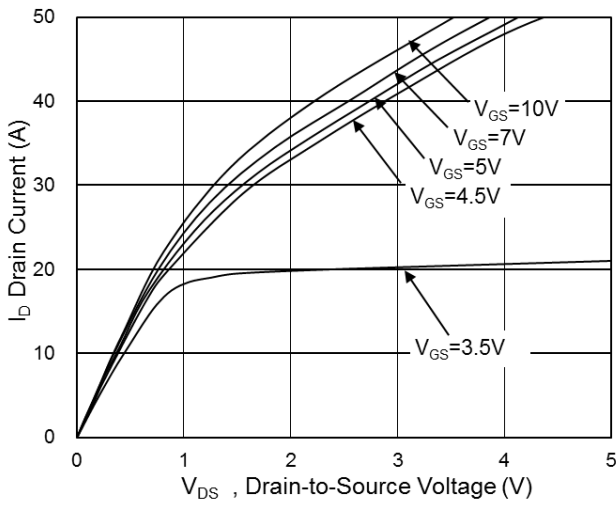
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V$ , Force Current	---	---	30	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=10A, dI/dt=100A/\mu s,$	---	35	---	nS
$Q_{rr}$	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	120	---	nC

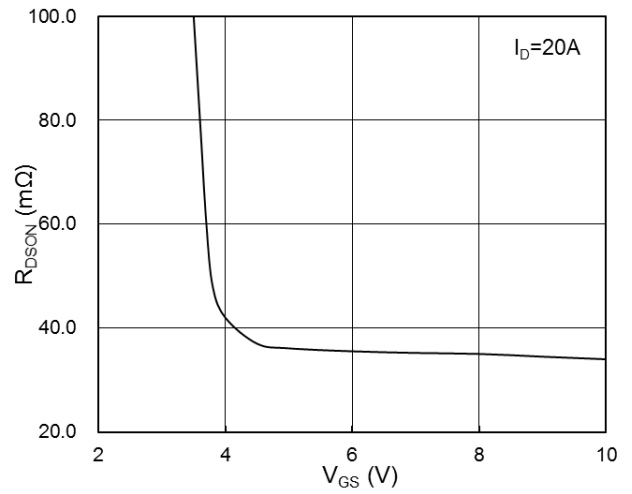
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.3mH, I_{AS}=38A$
- 4.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

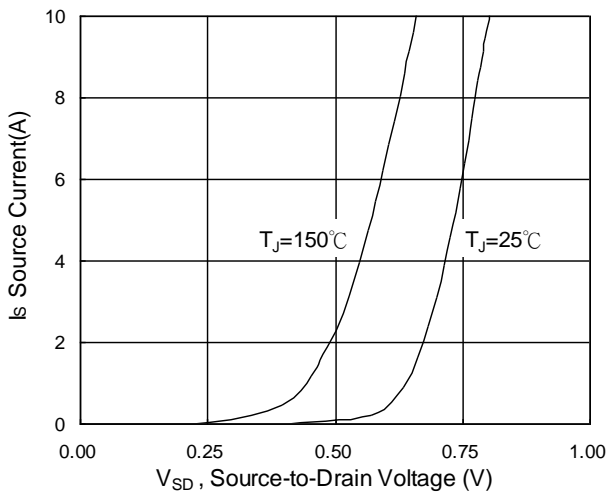
### Typical Characteristics



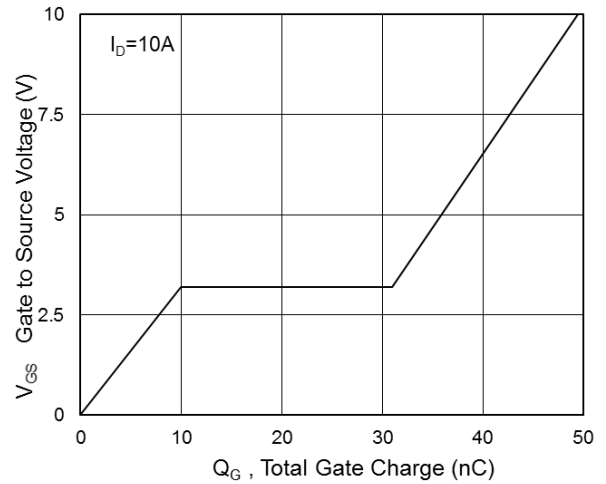
**Fig.1 Typical Output Characteristics**



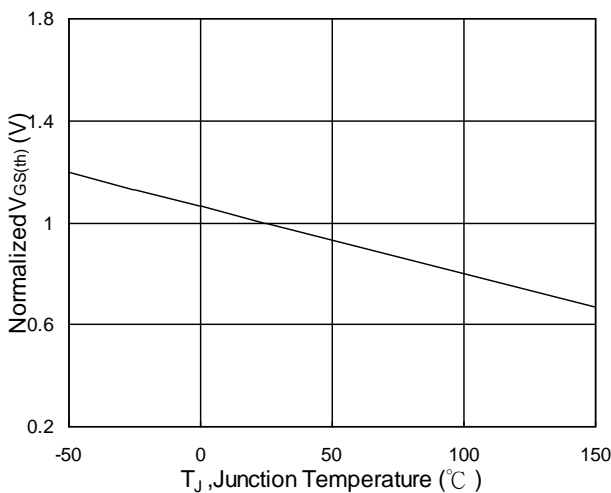
**Fig.2 On-Resistance vs. Gate-Source**



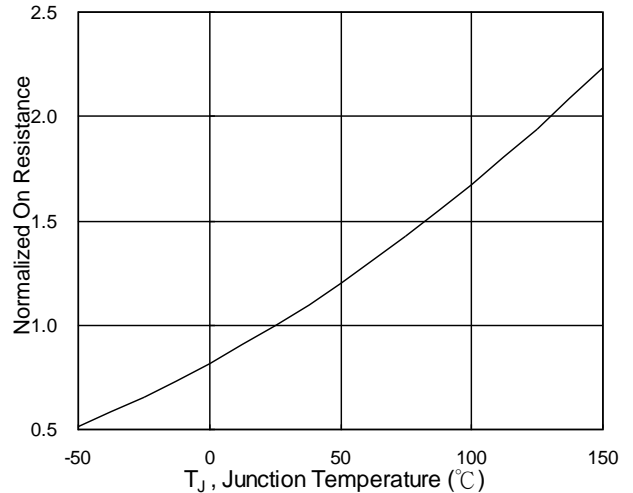
**Fig.3 Forward Characteristics Of Reverse**



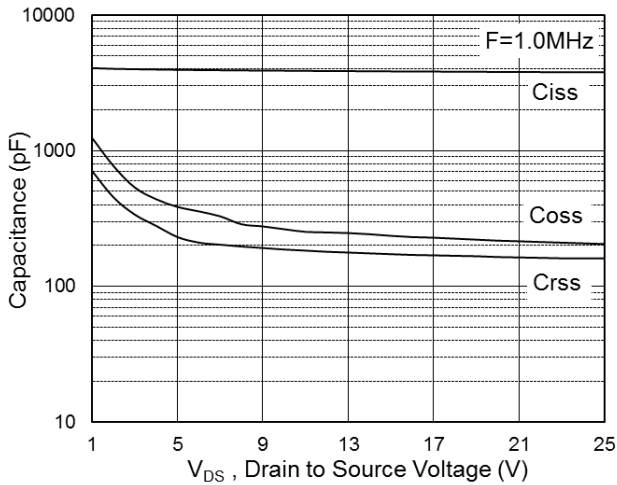
**Fig.4 Gate-Charge Characteristics**



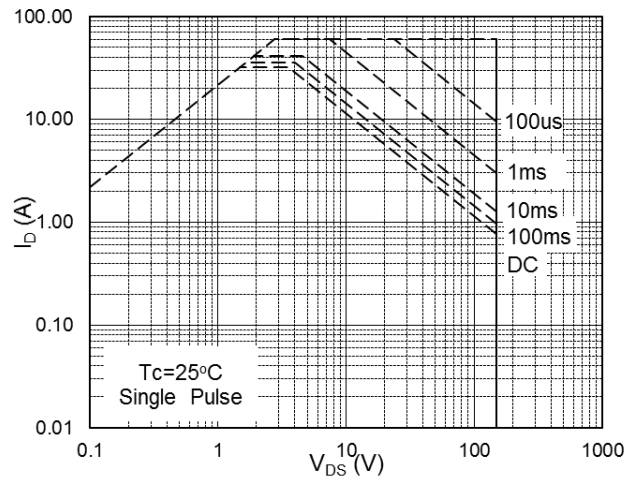
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



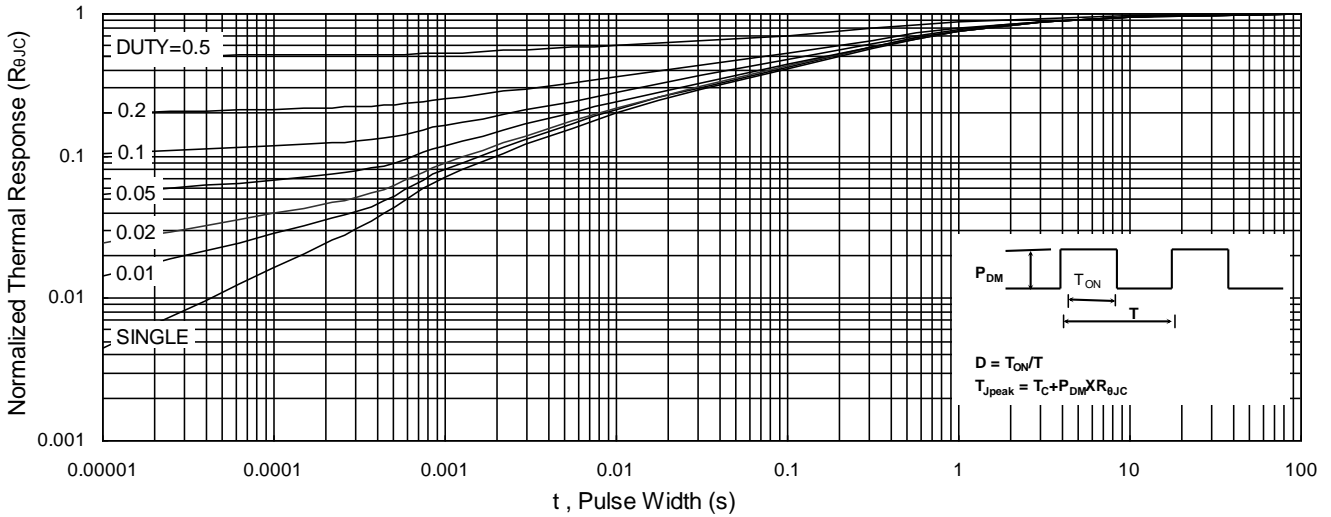
**Fig.6 Normalized  $R_{DSON}$  vs.  $T_J$**



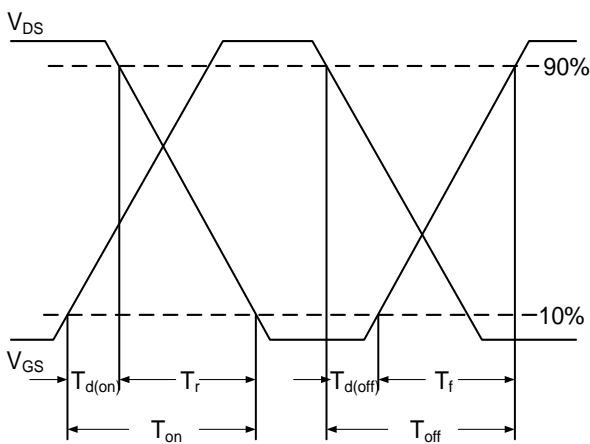
**Fig.7 Capacitance**



**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**